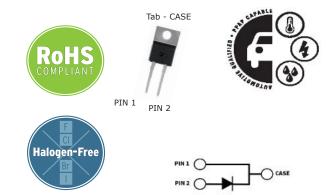


E-Series Automotive 650 V, 10 A Silicon Carbide Schottky Diode

Description

With the performance advantages of a Silicon Carbide (SiC) Schottky Barrier diode, power electronics systems can expect to meet higher efficiency standards than Si-based solutions, while also reaching higher frequencies and power densities. SiC diodes can be easily paralleled to meet various application demands, without concern of thermal runaway. In combination with the reduced cooling requirements and improved thermal performance of SiC products, SiC diodes are able to provide lower overall system costs in a variety of diverse applications.



Part Number	Package	Marking
E6D10065A	TO-220-2	E6D10065A

Features

- Low Forward Voltage (V_F) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior
- Automotive Qualified (AEC Q101) and PPAP Capable

Applications

- Interleaved or Bridgless PFC
- DC/DC On Board Battery Chargers
- Boost for PFC & DC-DC Stages
- AC/DC On Board Chargers
- PFC Output Rectification

Maximum Ratings ($T_c = 25^{\circ}$ C Unless Otherwise Specified)

Parameter	Symbol	Value	Unit	Test Conditions	Notes
Repetitive Peak Reverse Voltage	V _{RRM}	650			
Surge Peak Reverse Voltage	V _{RSM}	650	V		
DC Blocking Voltage	V _{DC}	650			
		34		T _c = 25 °C	
Continuous Forward Current	I _F	17		T _c = 125 °C	Fig. 3
		11	Α	T _c = 150 °C	
Repetitive Peak Forward Surge		45		T _c = 25 °C, t _p = 10 ms, Half Sine Wave	
Current	FRM	25		$T_c = 110 ^{\circ}\text{C}$, $t_p = 10 \text{ms}$, Half Sine Wave	
Non-Repetitive Forward Surge		82		T _c = 25 °C, t _p = 10 ms, Half Sine Wave	
Current	FSM	71	Α	$T_c = 110 ^{\circ}\text{C}$, $t_p = 10 \text{ms}$, Half Sine Wave	
B	_	94	,,,	T _c = 25 °C	<u>-</u>
Power Dissipation	P _{tot}	41	W	T _c = 110 °C	Fig. 4
	63.11	34		$T_c = 25 {}^{\circ}\text{C}, t_p = 10 \text{ms}$	
i²t value	∫i²dt	25	A ² s	$T_c = 110 ^{\circ}\text{C}, t_p = 10 \text{ms}$	

Electrical Characteristics

Parameter	Symbol	Тур.	Max.	Unit	Test Conditions	Notes
Famous and Malika are	V	1.3	1.5		I _F = 10 A, T _j = 25 °C	F:_ 1
Forward Voltage	V _F	1.4	1.6	V	I _F = 10 A, T _j = 175 °C	Fig. 1
Decrees Comment		1	50		$V_R = 650 \text{ V}, T_j = 25 \text{ °C}$	F:- 2
Reverse Current	I _R	10	200	μΑ	V _R = 650 V, T _j = 175 °C	Fig. 2
Total Capacitive Charge	Q_c	33.5		nC	$V_R = 400 \text{ V}, T_j = 25 \text{ °C}$	Fig. 5
		630			$V_R = 0 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$	
Total Capacitance	С	64		pF	$V_R = 200 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$	Fig. 6
		50			$V_R = 400 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$	
Capacitance Stored Energy	E _c	5.0		μJ	V _R = 400 V	Fig. 7

Notes:

SiC Schottky Diodes are majority carrier devices, so there is no reverse recovery charge.

Thermal & Mechanical Characteristics

Parameter	Symbol	Value	Unit	Notes
Thermal Resistance, Junction to Case (Typical)	R _{0, JC (TYP)}	1.24	°C/W	
Thermal Resistance, Junction to Case (Max)	R _{e, JC (MAX)}	1.60	°C/W	
Junction Temperature	T _j	-55 to +175		
Case & Storage Temperature	T _c	-55 to +175	°C	
		1	Nm	M3 Screw
TO-220 Mounting Torque	-	8.8	lbf-in	6-32 Screw

Typical Performance

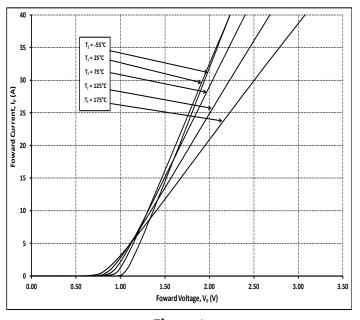
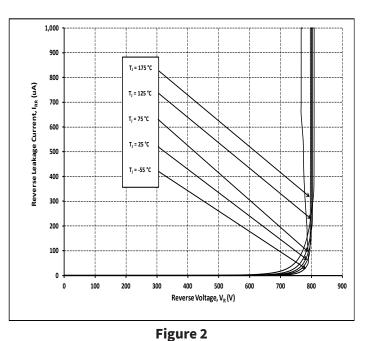


Figure 1Forward Characteristics



Reverse Characteristics

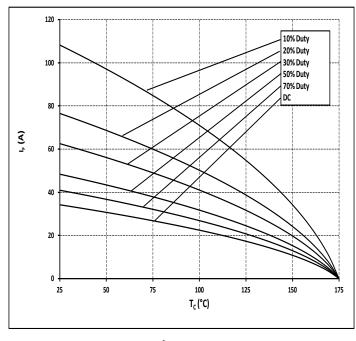


Figure 3Current Derating

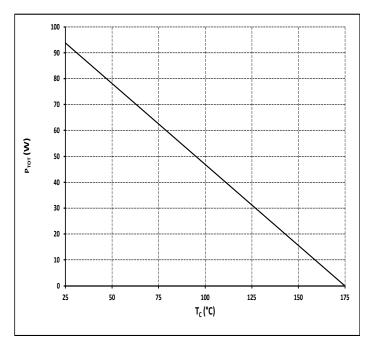


Figure 4Power Derating

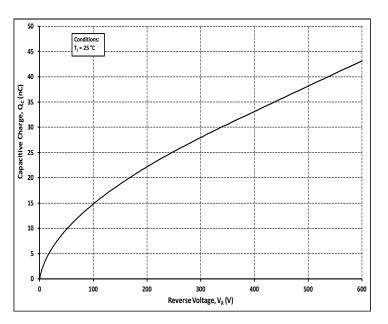


Figure 5Total Capacitance vs. Reverse Voltage

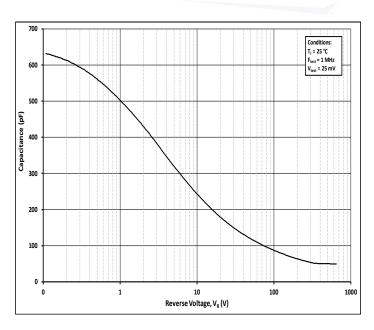


Figure 6Capacitace vs. Reverse Voltage

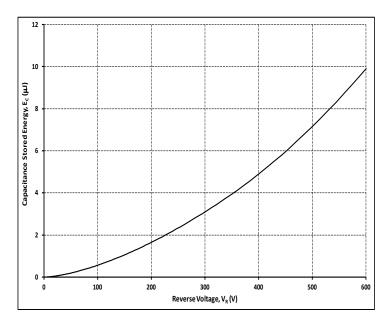


Figure 7Capacitance Stored Energy

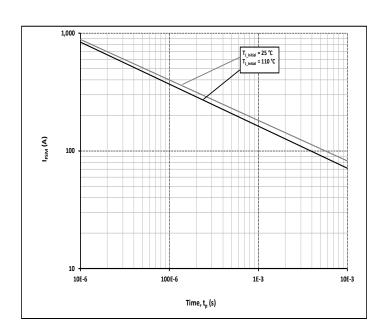


Figure 8Non Repetitive Peak Forward Surge Current versus Pulse Duration (sinsusoidal waveform)

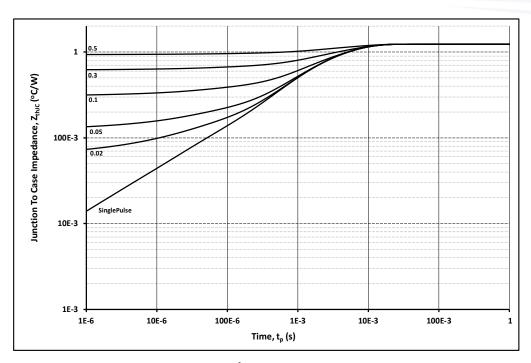
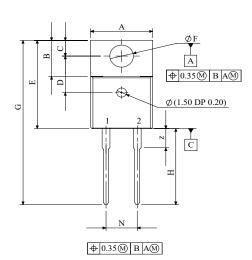
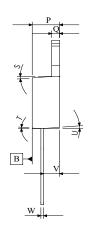


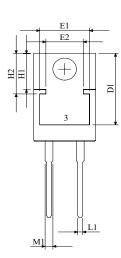
Figure 9Transient Thermal Impedance

Package Dimensions & Pin-Out

Package: TO-220-2









SYMBOL	MIN (mm)	MAX (mm)			
A	9.677	10.414			
В	5.969	6.477			
C	2.540	3.048			
D	5.664	8.560			
D1	12.450) REF			
E	14.986	15.621			
E1	8.120	REF			
E2	6.100	REF			
F	3.632	3.886			
G	28.067	29.134			
H	12.700	13.970			
H1	6.223 REF				
H2	7.040 REF				
L1	0.635	0.914			
M1	1.143	1.397			
N	4.953	5.207			
P	4.191	4.699			
Q	1.219	1.372			
S	3°	6°			
T	3°	6°			
U	3°	6°			
V	2.388	2.794			
W	0.356	0.635			
W1	0.356	0.520			
X	3°	5.5 °			
Y	9.779	10.414			
Z	3.302	3.810			

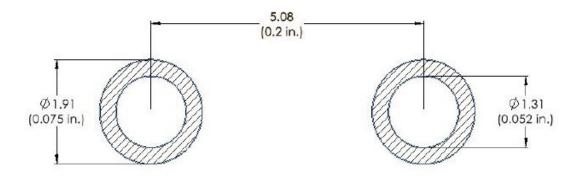
2 ANODE	1	CATHODE	
	2	ANODE	
3 CATHODE	3	CATHODE	

- 1. ALL METAL SURFACES ARE TIN PLATED (MATTE), EXCEPT AREA OF CUT.

 2. DIMENSIONING & TOLERANCING CONFORM TO
- ASME Y14.5M-1994.
- 3. ALL DIMENSIONS ARE LISTED IN MILLIMETERS. ANGLES ARE IN DEGREES.
- 4. PACKAGE BURR FLASH SIZE (0.5 mm) IS NOT INCLUDED IN THE DIMENSIONS

Recommended Solder Pad Layout

Primary dimensions shown in mm.



Product Ordering Information

Order Number	Packing Type
E6D10065A	Tube

Revision History

Document Version	Date of Release	Description of Changes
1	January 2024	Initial Release

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Contact info:

4600 Silicon Drive Durham, NC 27703 USA Tel: +1.919.313.5300 www.wolfspeed.com/power

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